



NPN BD683 – BD683A

SILICON DARLINGTON POWER TRANSISTORS

The BD683 and BD683A are NPN epitaxial-base transistors in monolithic Darlington circuit for audio and video applications.

They are mounted in Jedec TO-126 plastic package.

PNP complements are BD684 and BD684A.

Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
V_{CEO}	Collector-Emitter Voltage	120	V
V_{CBO}	Collector-Base Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	I_C	4
		I_{CM}	6
I_{BM}	Base current peak value	0.1	A
P_T	Total power Dissipation @ $T_{mb} = 25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{Stg}	Storage Temperature	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-mb}	Thermal Resistance, Junction to mounting base	3.12	K/W
R_{thJ-a}	Thermal Resistance, Junction to ambient in free air	100	K/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
I_{CBO}	Collector cut-off current	$I_E=0, V_{CB}= 120 V$	-	-	0,2	mA
		$I_E=0, V_{CB}= 120V, T_j= 150^\circ C$	-	-	2	
I_{CEO}	Collector cut-off current	$I_B=0, V_{CE}= 1/2V_{CEOMAX}$	-	-	0,5	mA
I_{EBO}	Emitter cut-offcurrent	$I_C=0, V_{EB}=5 V$	-	-	5	mA
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=1.5 A, I_B=30 mA$ BD683	-	-	2,5	V
		$I_C=2 A, I_B=40 mA$ BD683A	-	-	2,8	
h_{FE}	DC Current Gain (*)	$V_{CE}=3 V, I_C=1.5 A$ BD683	750	-	-	-
		$V_{CE}=3 V, I_C=2 A$ BD683A				
V_{BE}	Base-Emitter Voltage (*)	$V_{CE}=3 V, I_C=1.5 A$ BD683	-	-	2,5	V
		$V_{CE}=3 V, I_C=2 A$ BD683A				
h_{fe}	Small signal current gain	$V_{CE}=3 V, I_C=1.5 A, f= 1 MHz$	10	-	-	-
f_{hfe}	Ut-off frequency	$V_{CE}=3 V, I_C=1.5 A$	-	60	-	kHz
V_F	Diode forward voltage	$I_F=1,5 A$	-	1,5	-	V
$I_{(SB)}$	Second-breakdown collector current	$V_{CE}=50 V, t_p= 20ms, non rep. without heatsink$	0,8	-	-	A
t_{on}	Turn-on time	$I_{con}= 1.5A, -I_{bon}= I_{boff}= 6mA$ $V_{CC}=30V$	-	0,8	2	μs
t_{off}	Turn-off time		-	4,5	8	

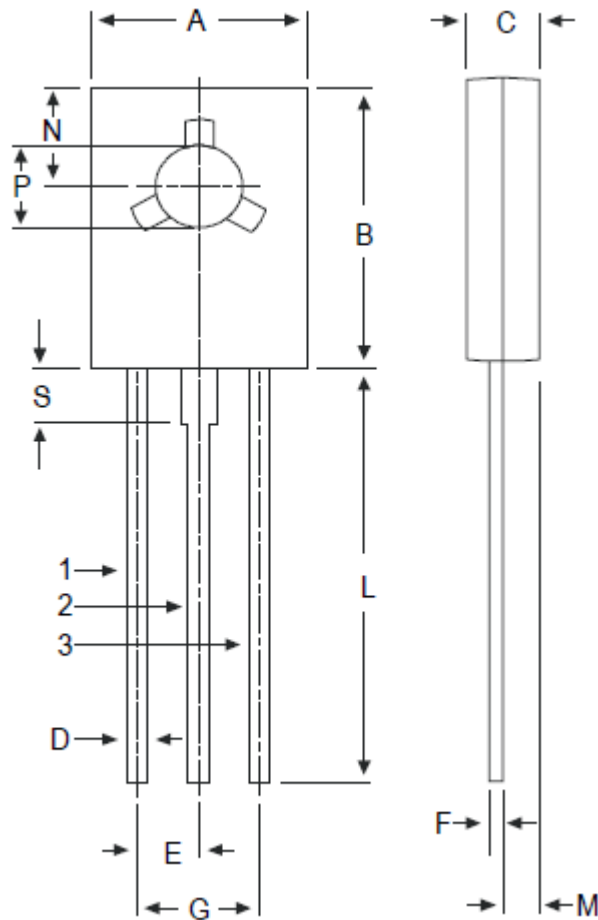
(*) Measured under pulse conditions : $t_p < 300\mu s, \delta < 2\%$.

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MECHANICAL DATA CASE TO-126

	DIMENSIONS	
	min	max
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 typ.	
F	0.49	0.75
G	4.4 typ.	
L	15.7 typ.	
M	1.27 typ.	
N	3.75 typ.	
P	3.0	3.2
S	2.54 typ.	

Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base



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